

Excellent Integrated System Limited

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Infineon Technologies SIDC42D170E6

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Distributor of Infineon Technologies: Excellent Integrated System Limited Datasheet of SIDC42D170E6 - DIODE GEN PURP 1.7KV 50A WAFER Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



SIDC42D170E6

Fast switching diode chip in Emitter Controlled -Technology

Features:

- 1700V technology, Emitter Controlled
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

 power modules and discrete devices



Applications:

• SMPS, resonant applications, drives

Chip Type	V _R	I _F	Die Size	Package
SIDC42D170E6	1700V	50A	6.5 x 6.5 mm ²	sawn on foil

Mechanical Parameter

Raster size	6.5 x 6.5		
Area total	42.25	mm ²	
Anode pad size	4.48 x 4.48		
Thickness	200	μm	
Wafer size	150	mm	
Max. possible chips per wafer	339		
Passivation frontside	Photoimide		
Pad metal	3200 nm AlSiCu		
Backside metal	Ni Ag-system suitable for epoxy and soft solder die bonding		
Die bond	Electrically conductive glue or solder	tive glue or solder	
Wire bond	Al, <i>≤</i> 500µm		
Reject ink dot size	Ø 0.65mm; max 1.2mm		
Recommended storage environment	Store in original container, in dry nitrogen, in dark environment, < 6 month at an ambient temperature of 23°C		



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Maximum Ratings

Parameter	Symbol	Condition	Value	Unit	
Repetitive peak reverse voltage	V _{RRM}	<i>T</i> _{vj} = 25 °C	1700	V	
Continuous forward current	/ _F	<i>T</i> _{vj} < 150°C	1)	- A	
Maximum repetitive forward current	I _{FRM}	<i>T</i> _{vj} < 150°C	100		
Junction temperature range	T _{vj}		-40+175	°C	
Operating junction temperature	T _{vj}		-40+150	°C	
Dynamic ruggedness ²⁾	P _{max}	$I_{\rm Fmax} = 100 {\rm A}, \ V_{\rm Rmax} = 1700 {\rm V}$ $T_{\rm vj} \le 150 {\rm ^{\circ}C}$	tbd	kW	

¹⁾ depending on thermal properties of assembly

²⁾ not subject to production test - verified by design/characterisation

Value Symbol Unit Parameter Conditions min. max. typ. Reverse leakage current $V_{\rm R} = 1700 \,\rm V$ 27 I_{R} μΑ Cathode - Anode 1700 V $I_{\rm R}$ = 4m A $V_{\rm BR}$ breakdown Voltage Diode forward voltage V_{F} I_F=50A 2.15 V

Static Characteristic (tested on wafer), Tvj = 25 °C

Further Electrical Characteristic

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

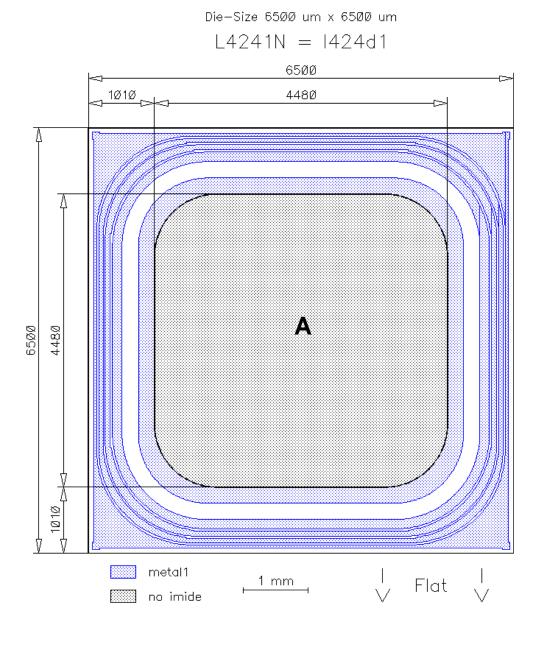


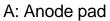
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Chip Drawing





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SIDC42D170E6

Description

AQL 0.65 for visual inspection according to failure catalogue

Electrostatic Discharge Sensitive Device according to MIL-STD 883

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